

full 1.126
sub

43. The method of claim 1, wherein forming a floating gate over
a substrate comprises:

3 forming the inner first portion in contact with a gate dielectric;

4 and

5 forming the outer second portion atop the inner first portion.

6
7 43. The method of claim 9, wherein forming a first layer
8 comprises forming a first layer of conductively doped polysilicon in
9 contact with a gate dielectric layer.

10
11 43. The method of claim 25, wherein forming a first layer of
12 poly silicon comprises forming a first layer of polysilicon in contact with
13 a gate dielectric layer.